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SOT23-3 N MOS

- CHANNEL MOSFET in a SOT23-3 Plastic Package.



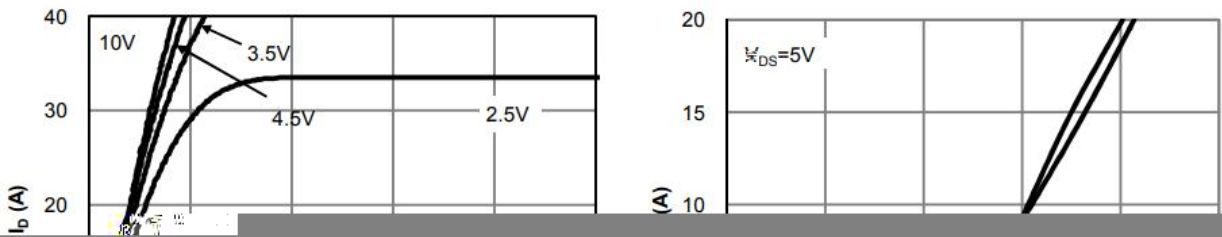
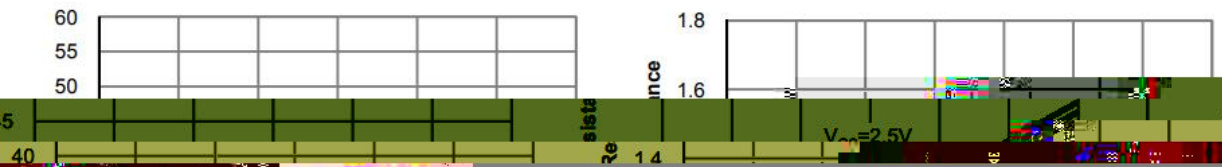
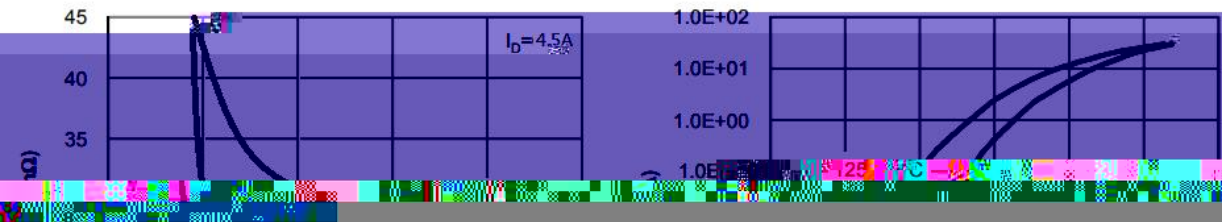
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Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±10	V
Drain Current – Continuous		I _D	4.5	A
Pulsed Drain Current		I _{DM}	12	A
Power Dissipation		P _D	1.4	W
Storage Temperature Range		T _{stg}	-55~150	℃
Maximum Junction-to-Ambient	t ≤ 10s	R _{θJA}	90	℃/W
Maximum Junction-to-Ambient				



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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Qg(10V)	$V_{GS}=10V, V_{DS}=10V$ $I_D=4.5A$		12.5		nC
Total Gate Charge	Qg(4.5V)			6		
Gate Source Charge	Qgs			1		
Gate Drain Charge	Qgd			2		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=10V$ $R_{GEN}=3\Omega, R_L=1.7\Omega$		3		ns
Turn-On Rise Time	t_r			7.5		
Turn-Off Delay Time	$t_{d(off)}$					
Turn-Off Fall Time						





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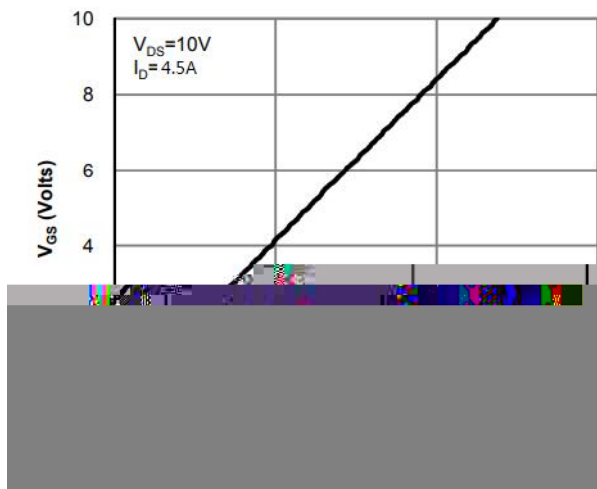
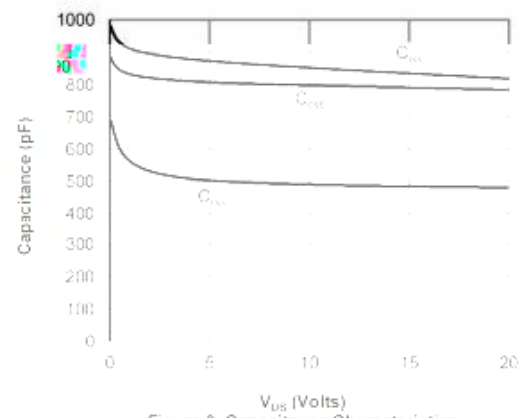
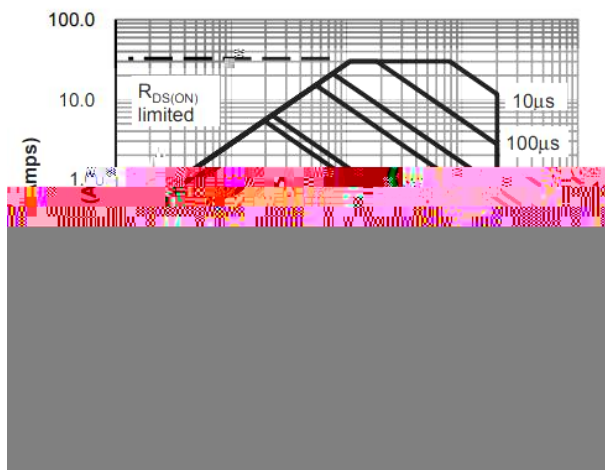
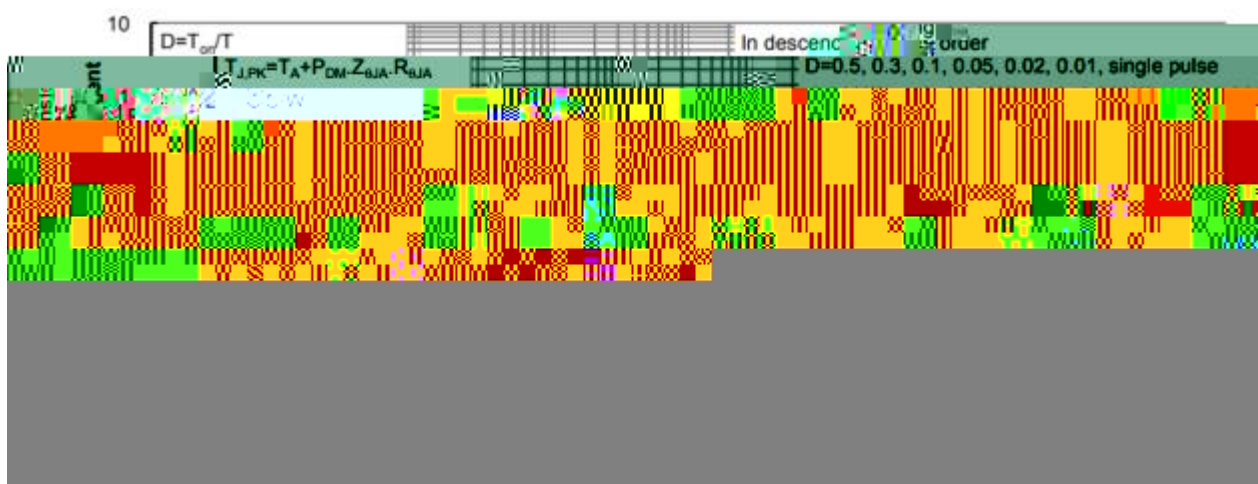
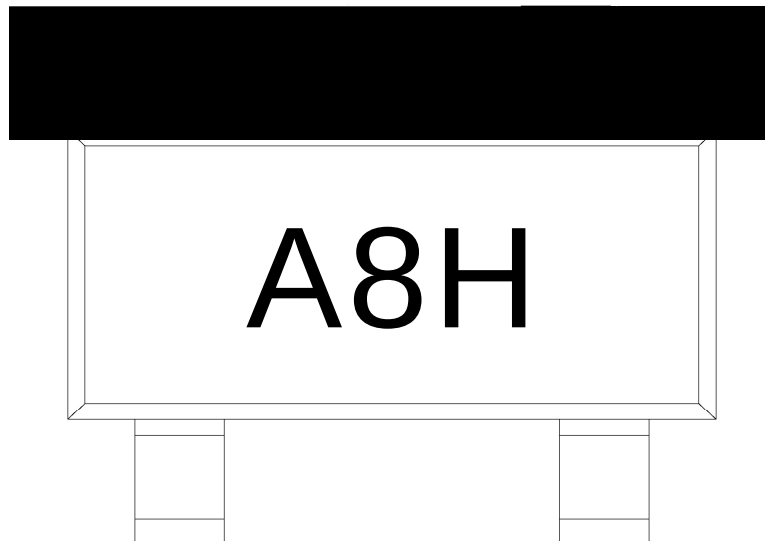


Figure 8: Capacitance Characteristics



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A8:

H:

Note:

A8 Product Type Code

H: Company Code.



Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1

150